LV8013T

Allowable Operating Conditions at $Ta = 25^{\circ}C$, SGND = PGND = 0V

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage (For load)	VM		2.0 to 15.0	V
Supply voltage (For control)	V _{CC}		2.7 to 5.5	V
Input signal voltage	VIN		0 to V _{CC}	V
Input signal frequency	f max	Duty = 50%	200	kHz
Capacitor for charge pump	C1, C2,		0.001 to 0.1	μF
	CVG1, CVG2			

Electrical Characteristics at $Ta = 25^{\circ}C$, $V_{CC} = 5.0V$, VM = 12.0V, SGND = PGND = 0V, unless especially specified.

Parameter		Symbol Conditions		Re-		Ratings		Unit
				marks	min	typ	max	Unit
Supply current for load at standby 1		IM1	EN = 0V	1			1.0	μΑ
Supply current for load at standby 2		IM2	V _{CC} = 0V, Each input = 0V	1			1.0	μΑ
Supply current for standby	or control at	ICO	EN = 0V, IN1 = IN2 = 0V	2	12.5	25	50	μA
Current drain du	ring operation 1	IC1	V_{CC} = 3.3V, EN = 3.3V, VG at no load	3		0.6	1.0	mA
Current drain du	ring operation 2	IC2	V_{CC} = 5.0V, EN = 5V, VG at no load	3		0.7	1.2	mA
H-level input vol	tage	VIH	$2.7V \le V_{CC} \le 5.5V$		0.6×V _{CC}		VCC	V
L-level input volt	age	VIL	$2.7V \le V_{CC} \le 5.5V$		0		0.2×V _{CC}	V
H-level input cur (IN1, IN2, TIN)	rrent	ЧН	V _{IN} = 5V	4	12.5	25	50	μΑ
L-level input current (IN1, IN2, TIN)		ΙIL	V _{IN} = 0V	4	-1.0			μΑ
Pull-up resistance (EN)		RUP		4	100	200	400	kΩ
Pull-down resista (EN)	ance	RDN		4	100	200	400	kΩ
Output ON resistance		RON	Sum of ON resistances at top and bottom	5		0.3	0.5	Ω
Charge pump voltage1		VG1	V _{CC} ×2 - 5.4V CLAMP circuit	6	5.15	5.4	5.65	V
Charge pump vo	oltage2	VG2	VM + VG1 Voltage raising circuit	6	17.1	17.4	17.6	V
Low-voltage dete voltage	ection operation	VCS	V _{CC} voltage	7	2.1	2.25	2.4	V
Thermal shutdov temperature	wn operation	Tth	Design guarantee	8	150	180	210	°C
Charge pump ca	apacity 1	VG1LOAD	IG1 = 500μA	9	5.0	5.3		V
Charge pump ca	apacity 2	VG2LOAD	IG2 = 500μA	9	16.0	16.5		V
IG current dissip (Fin = 20kHz)	pation	IG		10			350	μΑ
Charge pump st	art time	TVG	CVG = 0.1µF	11			1.0	ms
Output 1	Furn on time	TPLH		12		0.5	1.0	μS
block T	Furn off time	TPHL		12		0.5	1.0	μS
TOUT 1	Furn on time	TON	C = 500pF	12		0.5	20	μS
1	Furn off time	TOFF	C = 500pF	12		0.5	20	μS
TOUT output vo	Itage H	ТОН	C = 500pF		VG2-0.1	VG2		V
TOUT output voltage L		TOL	C = 500pF			0.05	0.1	V

* Design guarantee : This characteristics is not measured.

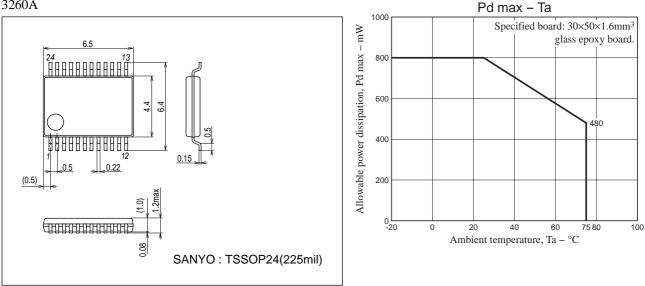
Refer to next page for remarks.

Remarks

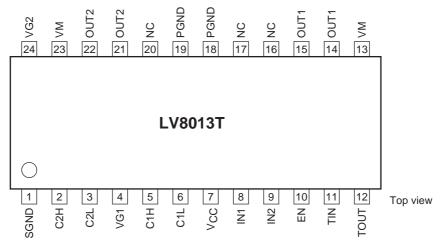
- 1. It shows current dissipation of VM pin in output OFF state.
- 2. It shows current dissipation of V_{CC} pin in stand-by state.
 - (The standard current depends on EN pin pull-down resistor.)
- 3. It shows current dissipation of V_{CC} pin in state of EN = 5V (stand-by), including current dissipation of VG pin.
- 4. IN1, IN2 and TIN pin are built-in pull-down resistor, EN pin is built-in pull-up resistor.
- 5. It shows sum of upper and lower saturation voltages of OUT pin.
- 6. It controls charge-pump oscillation and makes specified voltage.
- 7. When low voltage is detected, the lower output is turned OFF.
- 8. When thermal protection circuit is activated, the lower output is turned OFF. When the heat temperature is fallen, it is turned ON again.
- 9. IG (VG pin load current) = 500μ A
- 10. It shows VG pin current dissipation in state of PWM input for IN pin.
- 11. It specifies start-up time from 10% to 90% when VG is in non-load state (when setting the capacitor between VG and GND to 0.1μ F and V_{CC} is 5V).
- 12. It specifies 10% to 90% for start-up and 90% to 10% for shut-down.

Package Dimensions

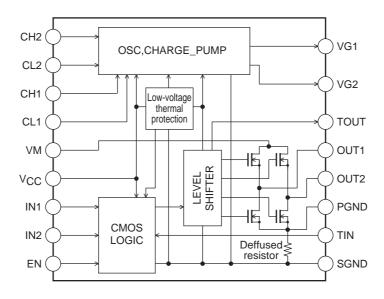
unit : mm (typ) 3260A



Pin Assignment



Block Diagram



Truth Table

EN	IN1	IN2	TIN	OUT1	OUT2	TOUT	Charge Pump	Mode
	н	Н	-	L	L	-	ON -	Brake
	н	L	-	Н	L	-		Forward
н	L	Н	-	L	н	-		Reverse
п	L	L	-	Z	Z	-		Standby
	-	-	L	-	-	L		Tr-OFF
	-	-	н	-	-	н		Tr-ON
L	-	-	-	L	L	L	OFF	Standby
							- : Don't	care, Z : High-Impedance

• Current drain becomes zero in the standby mode. (Leak current from EN pin is excluded)

• The output side becomes OFF, with motor drive stopped, during voltage reduction and thermal protection.

Also, the charge of VG2 is discharged with an internal circuit at decreasing voltage.

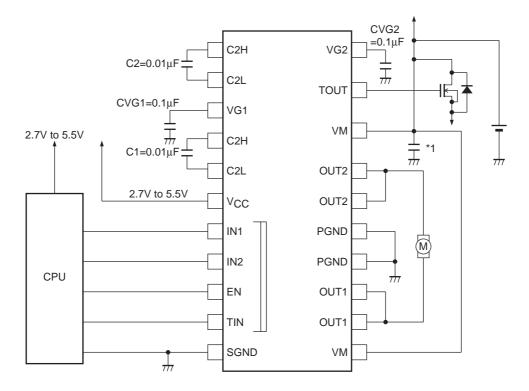
Pin No. Pin name Function Equivalent circuit 6 C1L Voltage raising capacitor connection pin. ∨сс C1L (5 C1H Voltage raising capacitor connection pin.) VG1 Ş C1H (IN1 8 · Driver output changeover. Vcc 9 IN2 TIN 11 · TOUT output control pin. ★ (Built-in pull-down resistor) ≷200kΩ ₩

Pin Function

Continued on next page.

Pin No.	Pin name	Function	Equivalent circuit
10	EN	Logic enable pin. (Built-in pull-up resistor)	
14 15 21 22 18 19	OUT1 OUT2 OUT2 PGND PGND	Driver output pin.	OUT1 OUT1 OUT2 OUT2 PGND
12	TOUT	Voltage raising output pin.	VG2
13 23	VM VM	Motor power supply. (both terminals to be connected)	
7	V _{CC}	Logic power supply.	
4	VG1	Voltage raising circuit 1. V _{CC} × 2 Clamped to 5.4V	C1H C1H C1L C1L C1L C1L C1L C1L C1L C1L
24 2 3	VG2 C2H C2L	 Voltage raising circuit 2. VM + VG1 Voltage raising capacitor connection pin. VG2 is discharged in abnormal. 	VM VG2 0.1µF C2H 0.01µF C2L 0.1µF
1	SGND	Logic GND	
18	PGND	Driver GND	
19	PGND	(both terminals to be connected)	

Application Circuit Example



- *1 : Connect a kickback absorption capacitor directly near IC. Coil kick-back may cause rise of the voltage of VM line, and the voltage exceeding the maximum rating may be applied momentarily, resulting in deterioration or damage of IC.
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